

A spot laser modulated resistance switching effect observed on *n*-type Mn-doped ZnO/SiO₂/Si structure

Supplementary information

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The evidence that the pre-prepared ZnO based film is *n*-type Mn-doped ZnO film.

Figure S1 SEM images for *n*-type Mn-doped ZnO film, the Mn target maintained at 5W during deposition process

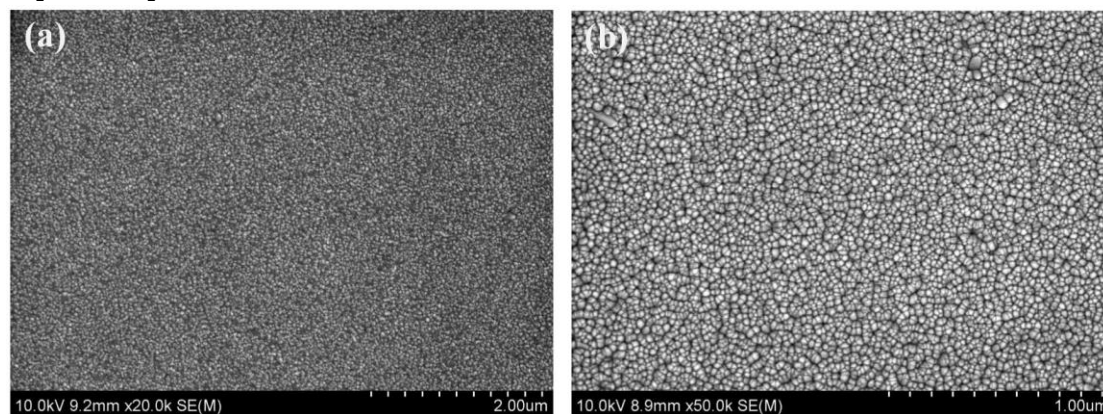


Figure S2 EDS elemental mapping results for area shown in Figure S1(a), showing that Al and Mn are well co-doped in ZnO in *n*-type Mn-doped ZnO film preparation.

